

Design of columnar quantum dots for polarization-independent emission using 8-band $k \cdot p$ method

J. Andrzejewski, G. Sęk, E. O'Reilly, A. Fiore, J. Misiewicz
Journal of Physics Conference Series **245** 012038 (2010)

Eight-band $k \cdot p$ calculations of the composition contrast effect on the linear polarization properties of columnar quantum dots

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Properties and preparation of high quality, free-standing GaN substrates and study of spontaneous separation mechanism

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Broadening of intersubband transitions in InGaN/AlInN multiquantum wells

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